

<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>		Application No.	10/568,229
(Multiple sheets used when necessary)		Filing Date	February 14, 2006
SHEET 1 OF 2		First Named Inventor	Vivian Alberts
		Art Unit	1793
		Examiner	Ip, Sikyin
		Attorney Docket No.	DMKISCH.003APC

<b>U.S. PATENT DOCUMENTS</b>					
Examiner Initials	Cite No.	Document Number Number - Kind Code (if known) Example: 1,234,567 B1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear

<b>FOREIGN PATENT DOCUMENTS</b>					
Examiner Initials	Cite No.	Foreign Patent Document Country Code-Number-Kind Code Example: JP 1234567 A1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear

<b>NON PATENT LITERATURE DOCUMENTS</b>		
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
1	V. Alberts, J. H. Schönh, and E. Bucher, <i>Journal of Appl. Phys.</i> , 84(12), 1998, 6881-6885, "Improved material properties of polycrystalline CuInSe <sub>2</sub> prepared by rapid thermal treatment of metallic alloys in H <sub>2</sub> Se/Ar."	T <sup>1</sup>
2	J. Palm, V. Probst, W. Stetter et al., <i>Thin Solid Films</i> , 451-452 (2004) 544-551, "CISSEs thin film PV modules: from fundamental investigations to advanced performance and stability."	
3	M. Marudachalam, H. Hichri, R. Klenk, R.W. Birkmire, W.N. Schafman and J. M. Schultz, <i>Appl. Phys. Lett.</i> 67(26), 1995, 3978, "Preparation of homogeneous Cu <sub>x</sub> (InGa) <sub>1-x</sub> Se <sub>2</sub> films by selenization of metal precursors in H <sub>2</sub> Se atmosphere."	
4	K. Kushiya, M. Tachiyuki, T. Kase, I. Sugiyama, Y. Nagoya, D. Okumura, M. Satoh, O. Yamase and H. Takeshita, <i>Sol. Energy Mater. Sol. Cells</i> 49, 1997, 277, "Fabrication of graded band-gap Cu <sub>x</sub> (InGa) <sub>1-x</sub> Se <sub>2</sub> thin-film mini-modules with a Zn(O <sub>x</sub> S <sub>y</sub> OH) <sub>z</sub> buffer layer."	
5	I. M. Kötschau, H. Kerber, H. Wiesner, G. Hanna and H. W. Schock, <i>Proceedings of the 16<sup>th</sup> European Photovoltaic Solar Energy Conference</i> , 1-5 May 2000, Glasgow, UK, pp. 724-727, "Band Gap Grading in Cu <sub>x</sub> (In <sub>1-x</sub> Ga) <sub>y</sub> (S,Se) <sub>1-y</sub> - based solar cells."	
6	R. Gay, M. Dietrich, C. Fredric, C. Jensen, K. Knappm, D. Tarrant and D. Willett, "Efficiency and process improvements in CuInSe <sub>2</sub> -based modules" <i>Proceedings of the international conference on E. C. Photovoltaic Solar Energy</i> , Vol. 12 (1), 1994, 935-938.	
7	T. Nakada, H. Ohbo, T. Watanabe, H. Nakazawa, M. Matsui and A. Kunioka, <i>Solar Energy Materials and Solar Cells</i> 49, 1997, 285, "Improved Cu <sub>x</sub> (In <sub>1-x</sub> Ga) <sub>y</sub> (S,Se) <sub>1-y</sub> thin film solar cells by solar sulfurization."	
8	A. Gupta and S. Isomura, <i>Sol. Energy Mater. Sol. Cells</i> 53, 1998, 385, "Precursor modification for preparation of CIS films by selenization technique."	
9	Office Action dated April 22, 2009 for U.S. Patent Application No. 10/568,227 filed May 17, 2006 (Attorney Docket no. DMKISCH.002APC)	

Examiner Signature	Date Considered
*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

T<sup>1</sup> - Place a check mark in this area when an English language Translation is attached.

<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>		Application No.	10/568,229
<i>(Multiple sheets used when necessary)</i>		Filing Date	February 14, 2006
SHEET 2 OF 2		First Named Inventor	Vivian Alberts
		Art Unit	1793
		Examiner	Ip, Sikyin
		Attorney Docket No.	DMKISCH.003APC

**NON PATENT LITERATURE DOCUMENTS**

Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>1</sup>
	10	"Experimental study of graded bandgap Cu(InGa)(SeS) <sub>2</sub> thin films grown on glass/molybdenum substrates by selenization and sulphidation" by Delsol et al. Solar Energy Materials a& Solar Cells 82 (2004) 587-599.	

7061065  
042809

Examiner Signature	Date Considered
*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

- Place a check mark in this area when an English language Translation is attached.